MY2300A

20V N-Channel Enhancement Mode MOSFET

MAOYUANWEI semiconductor

General Description

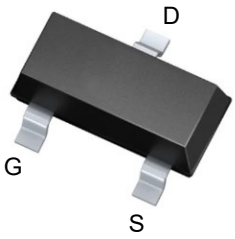
The MY2300A is the high cell density trenched N-CH MOSFET,which provides excellent $R_{DS(ON)}$ and efficiency for most of the small power switching and load switch applications.

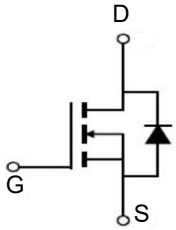
Features

V_{DSS}	20	V
I_D	6	A
$R_{DS(ON)}$(atV_{GS} =4.5V)	20	mΩ
$R_{DS(ON)}$(atV_{GS} =2.5V)	30	mΩ

Application

- Green Device Available
- Super Low Gate Charge
- Excellent Cdv/dt effect decline





Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
MY2300A	SOT-23-3L	MY2300A	3000

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	±12	
Continuous Drain Current	I_D	6	A
Pulsed Drain Current	I_{DM}	25	
Maximum Body-Diode Continuous Current	I_S	2	
Power Dissipation	P_D	0.35	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	357	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{stg}	-55 ~+150	

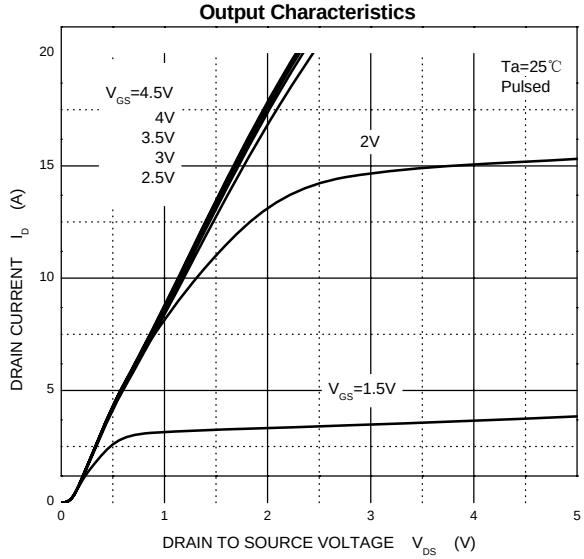
Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC PARAMETERS						
Drain-source breakdown voltage	$V_{(BR)\ DSS}$	V_{GS} = 0V, I_D =250μA	20			V
Gate-source leakage current	I_{GSS}	V_{DS} =0V, V_{GS} =±12V			±100	nA
Zero gate voltage drain current	I_{DSS}	V_{DS} =16V, V_{GS} =0V			1.0	μA
Gate threshold voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =250μA	0.5	0.7	1.0	V
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS} =4.5V, I_D =5.0A		20	30	mΩ
		V_{GS} =2.5V, I_D =4.0A		30	40	
		V_{GS} =1.8V, I_D =2.0A			73	
Diode forward voltage	V_{SD}	V_{GS} =0V,I_S=1A		0.75	1	V
Forward transconductance	g_{fS}	V_{DS} =5V, I_D =3.8A	4			S
DYNAMIC PARAMETERS*						
Input capacitance	C_{iss}	V_{DS} =10V,V_{GS} =0V,f =1MHz		630		pF
Output capacitance	C_{oss}			164		
Reverse transfer capacitance	C_{rss}			137		
Gate resistance	R_g	V_{DS} =0V,V_{GS} =0V,f =1MHz		1.5		Ω
SWITCHING PARAMETERS*						
Turn-on delay time	$t_{d(on)}$	V_{GS}=5V,V_{DS}=10V, R_L=1.7Ω,R_{GEN}=6Ω		5.5		ns
Rise time	t_r			14		
Turn-off delay time	$t_{d(off)}$			29		
Fall time	t_f			10.2		

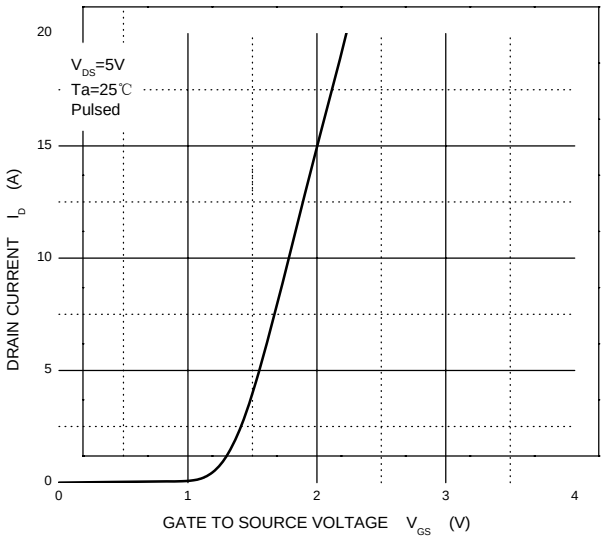
*These parameters have no way to verify.

Typical Electrical and Thermal Characteristics

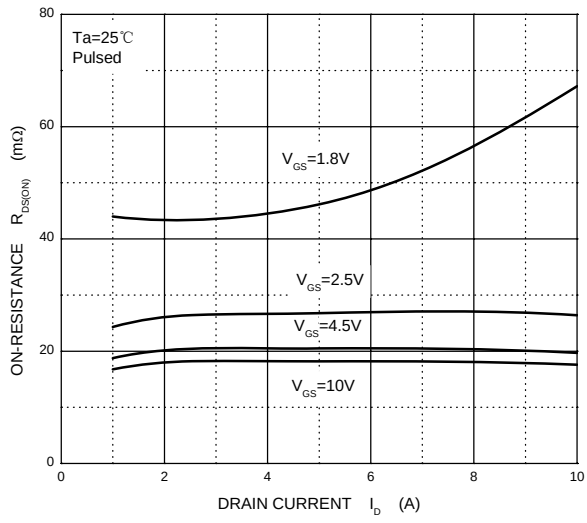
Output Characteristics



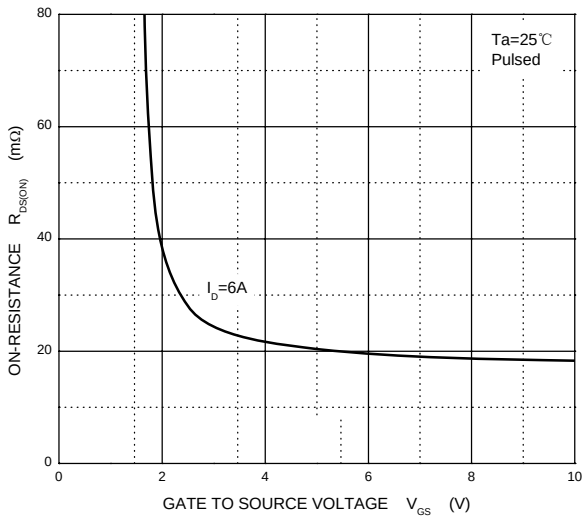
Transfer Characteristics



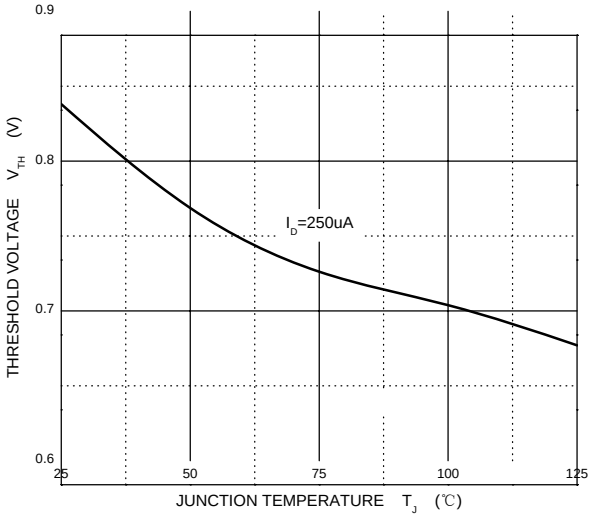
$R_{DS(ON)}$ — I_D



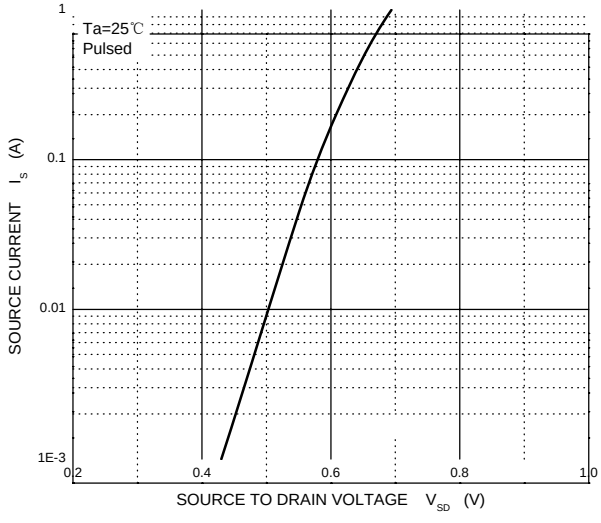
$R_{DS(ON)}$ — V_{GS}



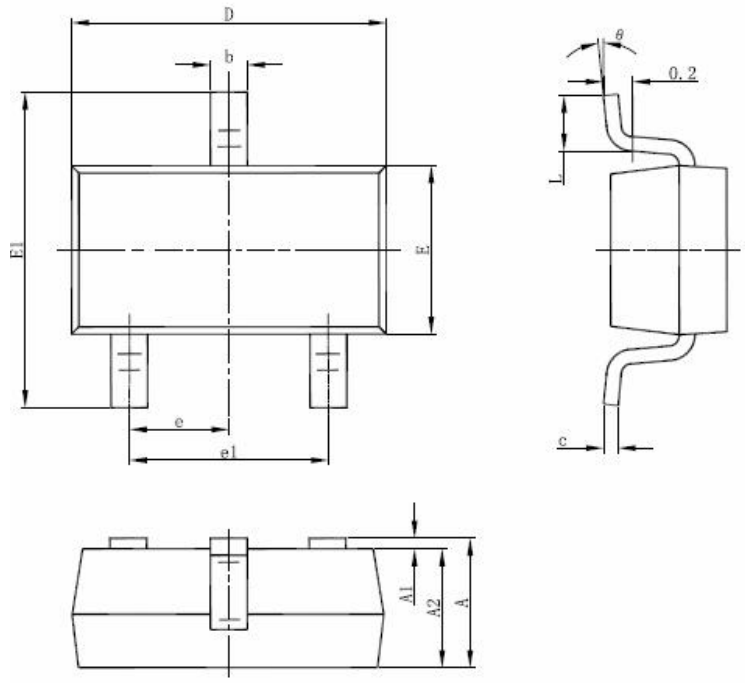
Threshold Voltage



I_S — V_{SD}



Package Mechanical Data-SOT-23-3L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°